

FEATURES

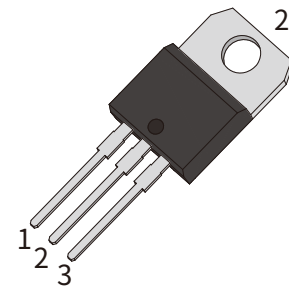
- | Glass-passivated mesa chip for reliability and uniform
- | High current output up to 25A

APPLICATIONS

- | Motor cycle
- | Power charger
- | T-tools etc

APPROVALS

RoHS	Compliance with 2011/65/EU
HF	Compliance with IEC61249-2-21:2003



TO-220B(Non-Ins)



Schematic Symbol

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1200	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1200	
RMS on-state current ($T_c=95^\circ\text{C}$)	$I_{\text{T(RMS)}}$	25	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}$)	I_{TSM}	300	
I^2t value for fusing ($t_p=10\text{ms}$)	I^2t	450	A^2S
Critical rate of rise of on-state current ($I_G=2 \times I_{\text{GT}}$)	di/dt	50	$\text{A}/\mu\text{s}$
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{\text{G(AV)}}$	1	W
Storage junction temperature range	T_{STG}	-40~+150	$^\circ\text{C}$
Operating junction temperature range	T_j	-40~+125	

ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

Symbol	Test Condition	Value	Unit
I _{GT}	V _D =12V, R _L =33Ω	≤40	mA
V _{GT}		≤1.3	V
V _{GD}	V _D =V _{DRM} , R _L =3.3KΩ, T _j =150°C	≥0.2	
I _H	I _T =500mA	≤80	mA
I _L	I _G =1.2I _{GT}	≤90	
dV _D /dt	V _D =2/3, V _{DRM} , Gate Open, T _j =150°C	≥200	V/μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value	Unit
V _{TM}	I _{TM} =50A,tp=380μs	T _j =25°C	≤1.55	V
I _{DRM}	V _D =V _{DRM} , V _R =V _{RRM}		≤10	uA
I _{RRM}		T _j =150°C	≤4	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case(AC)	1.0	°C/W

PARAMETER CHARACTERISTIC CURVE

FIG.1 Maximum power dissipation versus RMS on-state current

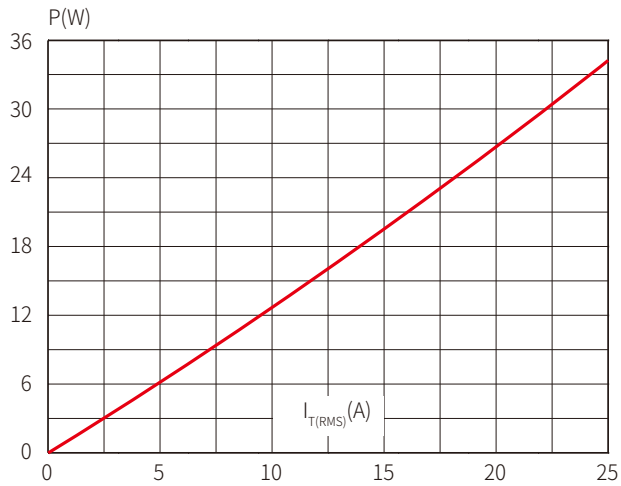


FIG.2: RMS on-state current versus case temperature

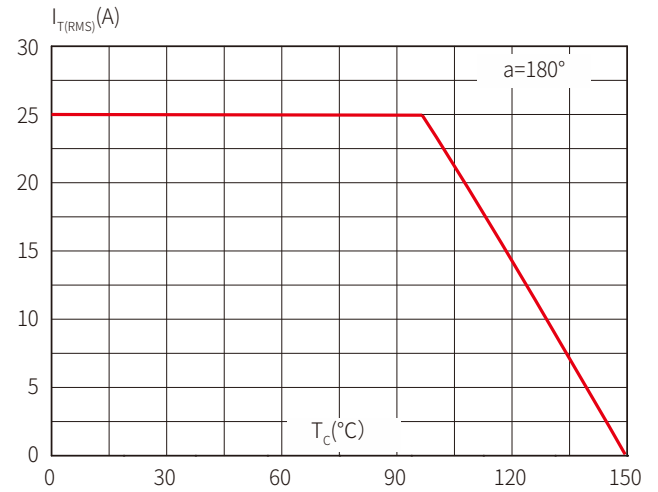


FIG.3: Surge peak on-state current versus number of cycles

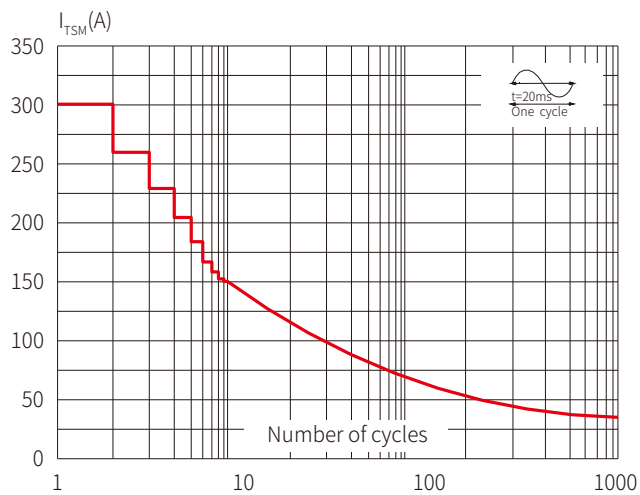


FIG.4 On-state characteristics (maximum values)

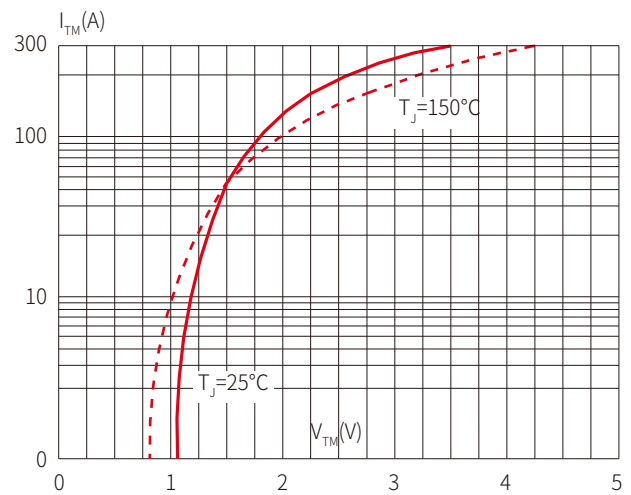


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$ and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

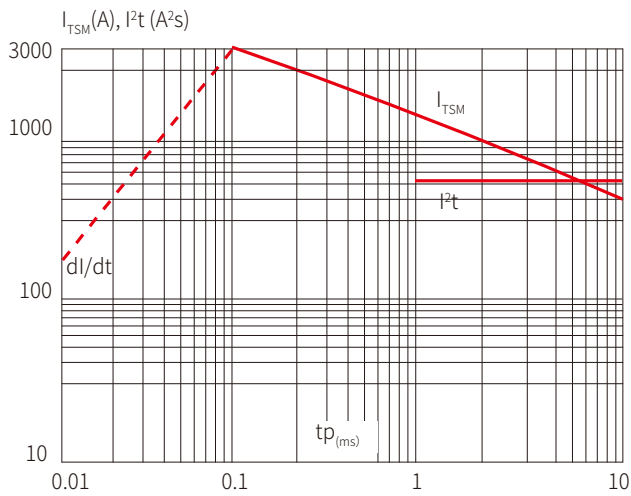


FIG.6 Relative variations of gate trigger current, holding current and latching current versus junction temperature

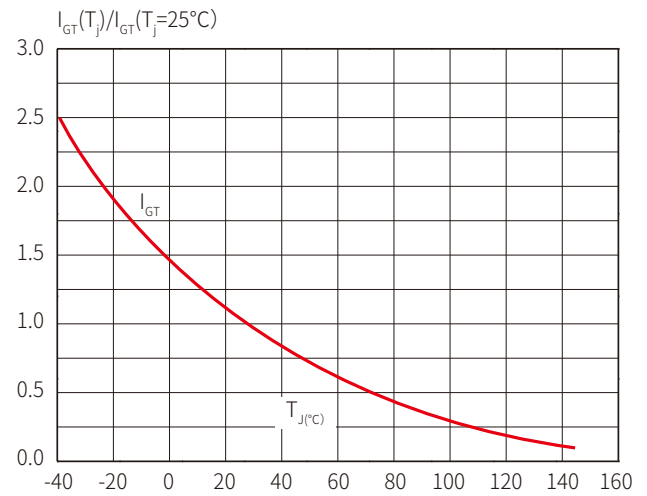


FIG.7 Relative variations of holding current versus junction temperature

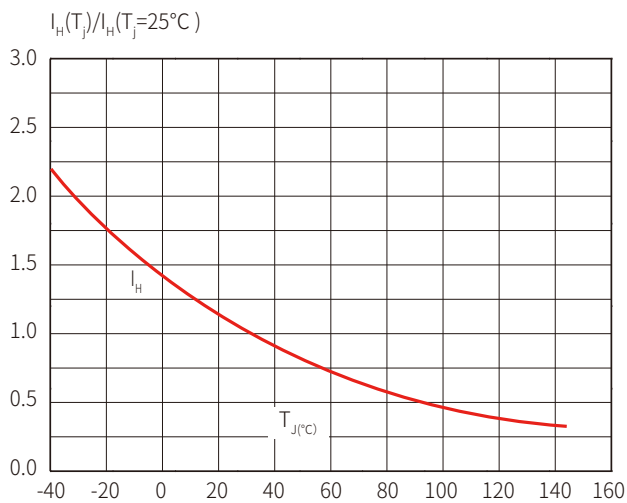
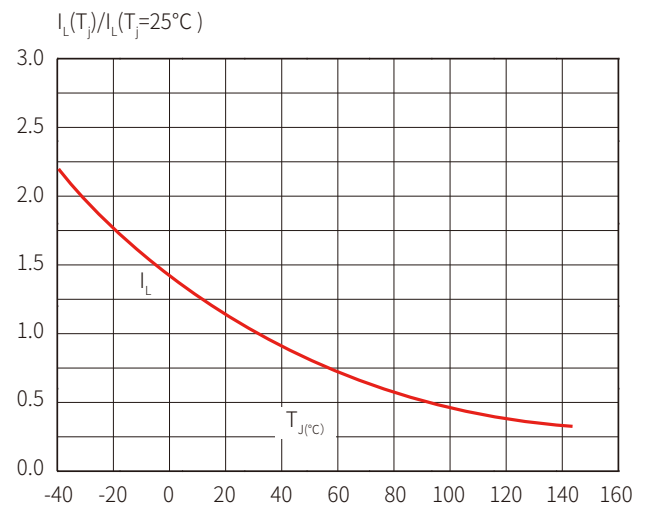
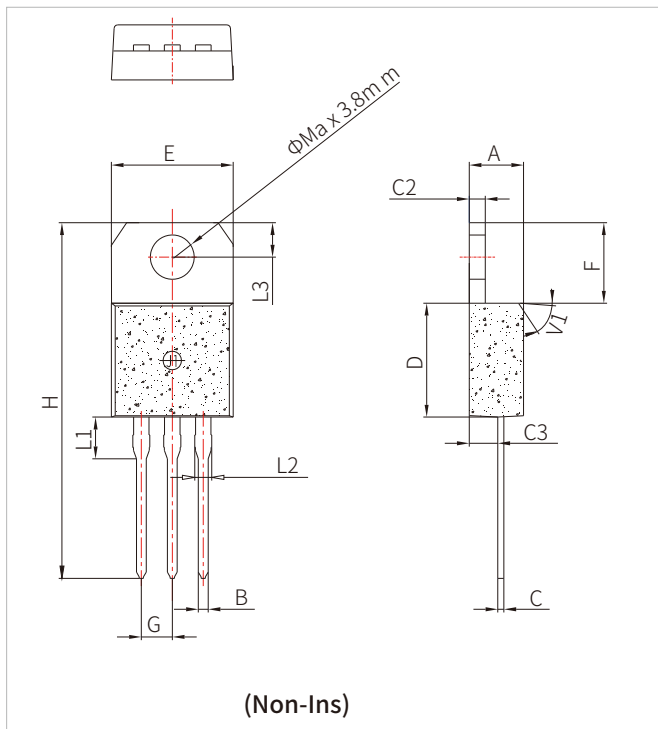


FIG.8 Relative variations of latching current versus junction temperature



TO-220B PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.70	0.169		0.185
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

ORDERING INFORMATION

Part Number	Package	Qty/pcs		
		Tube	Inner Box	Carton
SCB25C120	TO-220B	50	1000	5000

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By QR Code

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